

## Mosfet

Metal Oxide Semiconductor Field Effect Transistor

## OptiMOS™ Power-Transistor, -30V

BSL303SPE

## Data Sheet

Rev. 2.0  
Final

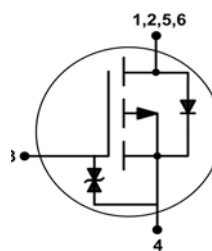
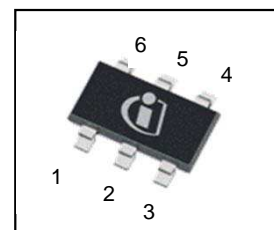
Industrial & Multimarket

**OptiMOS™-P 3 Small-Signal-Transistor**
**Features**

- P-channel
- Enhancement mode
- Logic level (4.5V rated)
- ESD protected
- Avalanche rated
- Qualified according to AEC Q101
- 100% Lead-free; RoHS compliant, halogen free


**Product Summary**

$V_{DS}$	-30	V
$R_{DS(on),max}$	$V_{GS}=-10\text{ V}$	33
	$V_{GS}=-4.5\text{ V}$	52
$I_D$	-6.3	A


**PG-TSOP-6**


Type	Package	Tape and Reel Information	Marking	Hal. Free	Packing
BSL303SPE	PG-TSOP-6	H6327: 3000 pcs/ reel	sPV	Yes	Non dry

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	$I_D$	$T_A=25\text{ °C}$	-6.3	A
		$T_A=70\text{ °C}$	-5.0	
Pulsed drain current	$I_{D,pulse}$	$T_A=25\text{ °C}$	-25.2	
Avalanche energy, single pulse	$E_{AS}$	$I_D=-6.3\text{ A}$ , $R_{GS}=25\ \Omega$	30.0	mJ
Reverse diode $dv/dt$	$dv/dt$	$I_D=-6.3\text{ A}$ , $V_{DS}=-15\text{ V}$ , $di/dt=100\text{ A}/\mu\text{s}$ , $T_{j,max}=150\text{ °C}$	6	kV/ $\mu\text{s}$
Gate source voltage	$V_{GS}$		$\pm 20$	V
Power dissipation	$P_{tot}$	$T_A=25\text{ °C}$	2.0	W
Operating and storage temperature	$T_j$ , $T_{stg}$		-55 ... 150	$^{\circ}\text{C}$
ESD Class		JESD22-A114 -HBM	2 (2KV to 4kV)	V
Soldering Temperature			260 $^{\circ}\text{C}$	$^{\circ}\text{C}$
IEC climatic category; DIN IEC 68-1			55/150/56	$^{\circ}\text{C}$

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Thermal characteristics**

Thermal resistance, junction - minimal footprint	$R_{thJS}$		-	-	50	K/W
SMD version, device on PCB	$R_{thJA}$	minimal footprint	-	-	230	
		6 cm <sup>2</sup> cooling area <sup>1)</sup>	-	-	62.5	

**Electrical characteristics, at  $T_j=25\text{ °C}$ , unless otherwise specified**
**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=0V, I_D=-30\mu A$	-2	-1.5	-1	
Drain-source leakage current	$I_{DSS}$	$V_{DS}=-30V, V_{GS}=0V, T_j=25\text{ °C}$	-	-	-0.1	$\mu A$
		$V_{DS}=-30V, V_{GS}=0V, T_j=150\text{ °C}$	-	-	-20	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=-20V, V_{DS}=0V$	-	-	-7	$\mu A$
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-5A$	-	35	52	m $\Omega$
		$V_{GS}=-10V, I_D=-6.3A$	-	25	33	
Transconductance	$g_{fs}$	$ V_{DS} >2 I_D R_{DS(on)max}, I_D=-5A$		12.9	-	S

<sup>1)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (single layer, 70  $\mu m$  thick) copper area for drain connection. PCB is vertical in still air. ( $t < 5$  sec.)

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics<sup>2)</sup>**

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=-15\text{ V},$ $f=1\text{ MHz}$	-	1053	1401	pF
Output capacitance	$C_{oss}$		-	482	641	
Reverse transfer capacitance	$C_{rss}$		-	33	50	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=-15\text{ V}, V_{GS}=-$ $10\text{ V}, I_D=-6.3\text{ A},$ $R_{G,ext}=6\ \Omega$	-	8.0	12	ns
Rise time	$t_r$		-	7.7	12	
Turn-off delay time	$t_{d(off)}$		-	23.7	36	
Fall time	$t_f$		-	8.3	12	

**Gate Charge Characteristics<sup>2)</sup>**

Gate to source charge	$Q_{gs}$	$V_{DD}=-15\text{ V}, I_D=-6.3\text{ A},$ $V_{GS}=0\text{ to }-10\text{ V}$	-	3.3	4.4	nC
Gate to drain charge	$Q_{gd}$		-	1.6	2.4	
Gate charge total	$Q_g$		-	14.0	20.9	
Gate plateau voltage	$V_{plateau}$		-	3.1	-	V

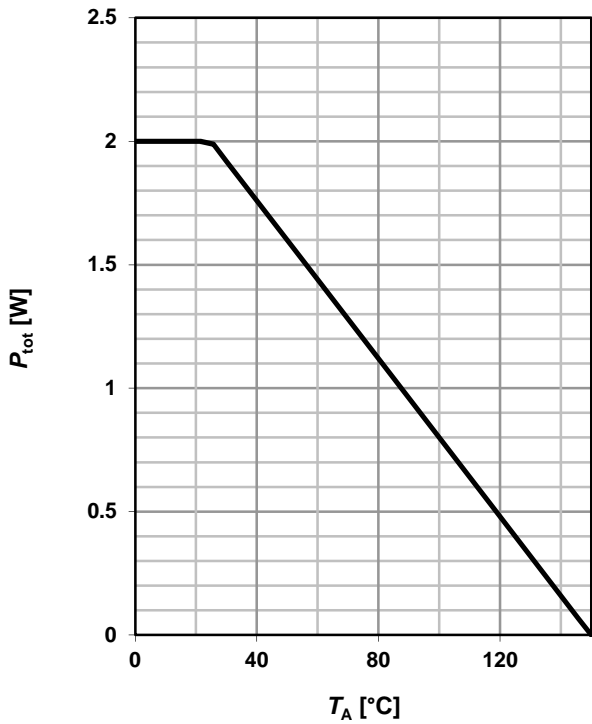
**Reverse Diode**

Diode continuous forward current	$I_S$	$T_A=25\text{ }^\circ\text{C}$	-	-	-6.3	A
Diode pulse current	$I_{S,pulse}$		-	-	-25.2	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=-6.3\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	-0.9	-1.1	V
Reverse recovery time <sup>2)</sup>	$t_{rr}$	$V_R=-15\text{ V}, I_F=-6.3\text{ A},$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	33	49	ns
Reverse recovery charge <sup>2)</sup>	$Q_{rr}$		-	28	43	nC

<sup>2)</sup> Defined by design. Not subjected to production test

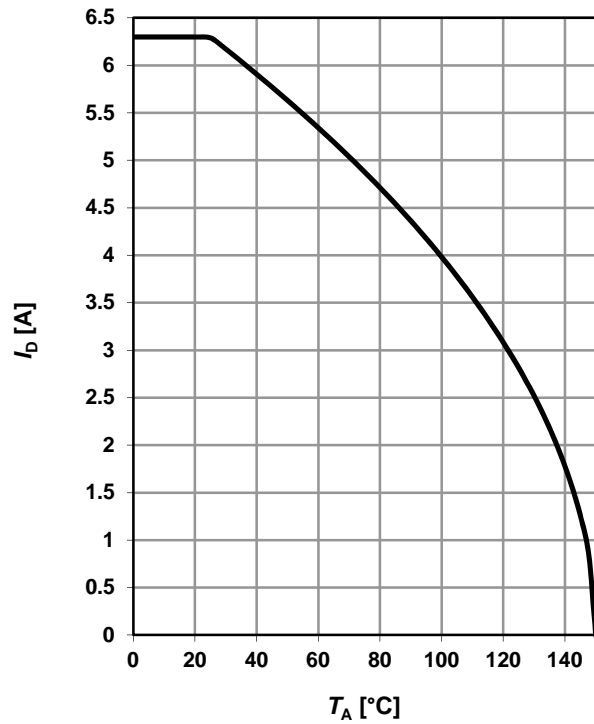
**1 Power dissipation**

$P_{tot}=f(T_A)$



**2 Drain current**

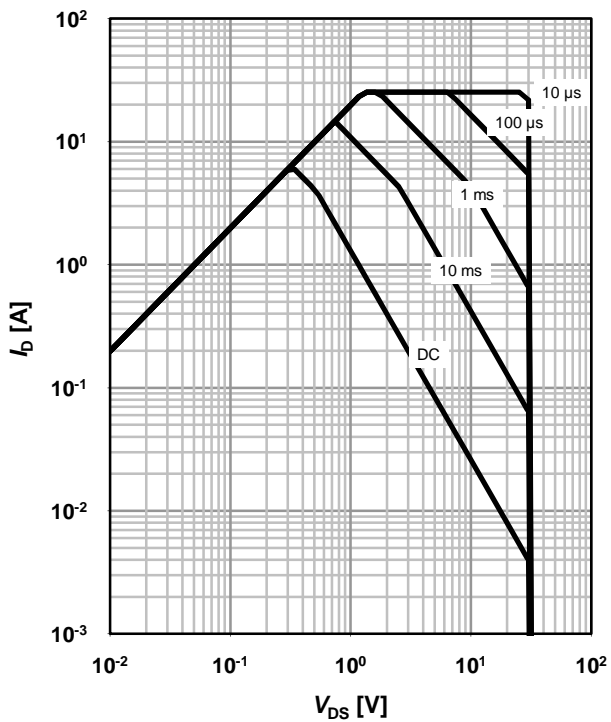
$I_D=f(T_A); V_{GS} \leq -10\text{ V}$



**3 Safe operating area**

$I_D=f(V_{DS}); T_A=25\text{ °C}; D=0$

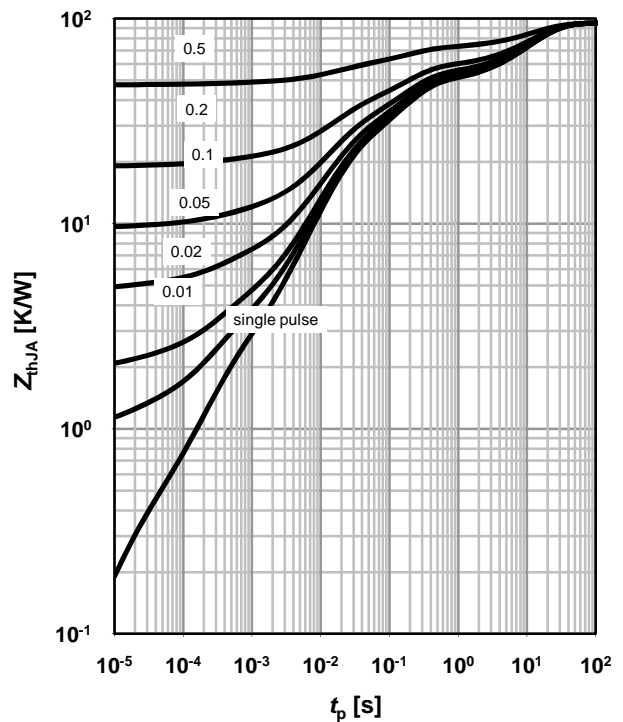
parameter:  $t_p$



**4 Max. transient thermal impedance**

$Z_{thJA}=f(t_p)$

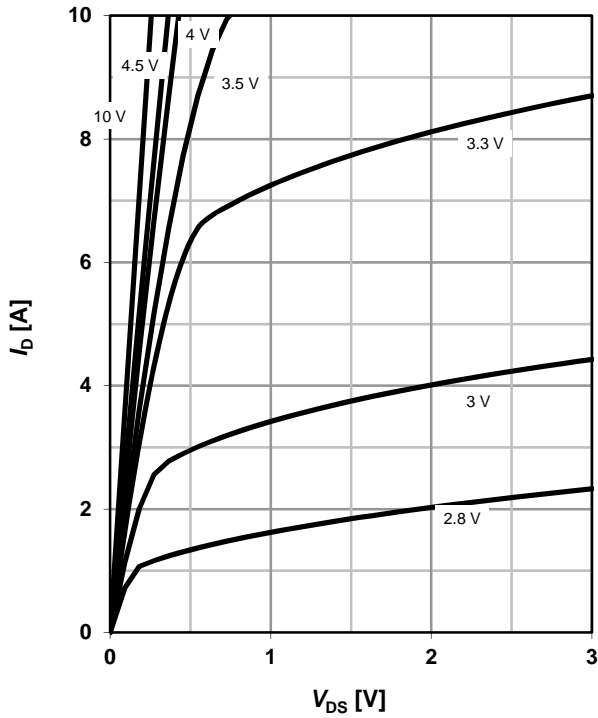
parameter:  $D=t_p/T$



**5 Typ. output characteristics**

$I_D=f(V_{DS}); T_j=25\text{ }^\circ\text{C}$

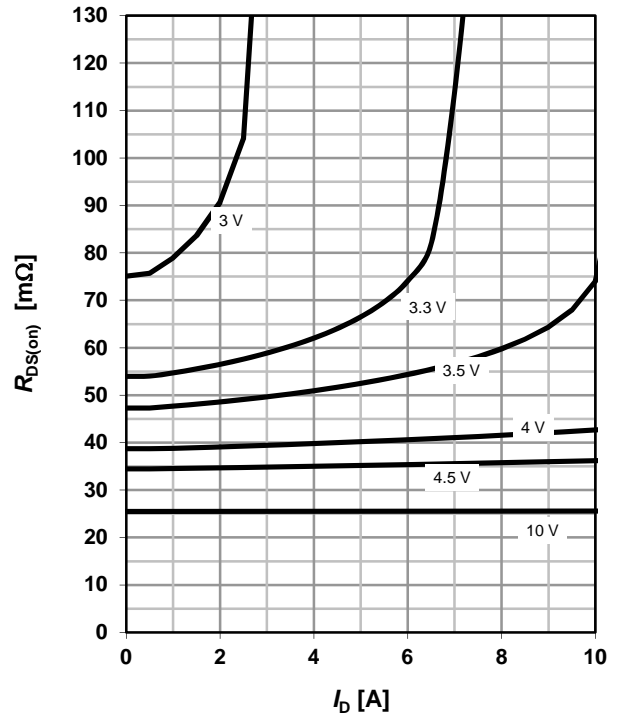
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

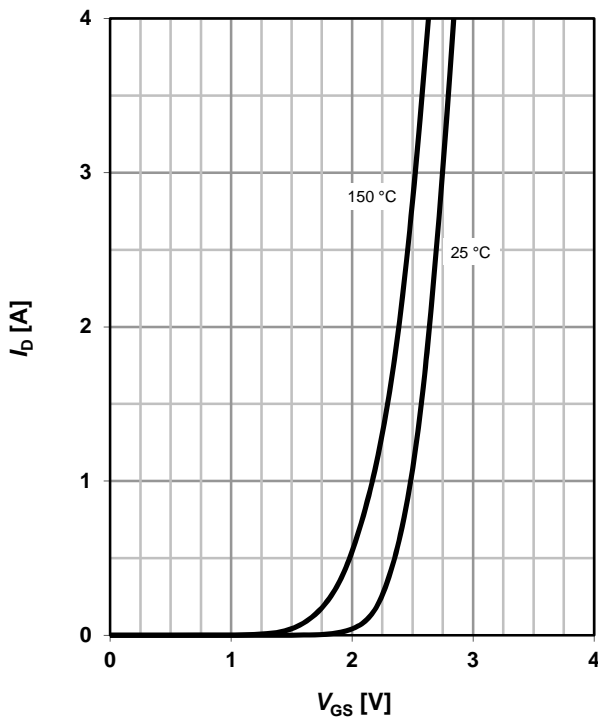
$R_{DS(on)}=f(I_D); T_j=25\text{ }^\circ\text{C}$

parameter:  $V_{GS}$



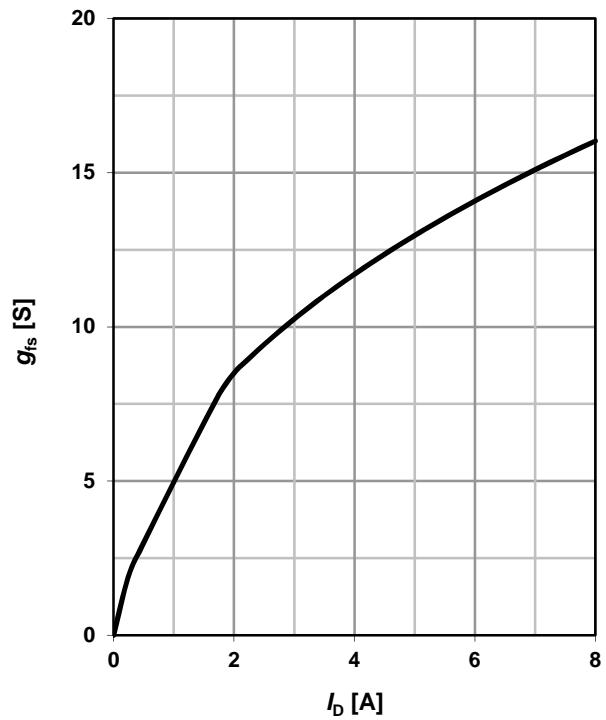
**7 Typ. transfer characteristics**

$I_D=f(V_{GS}); |V_{DS}|>2|I_D|R_{DS(on)max}$



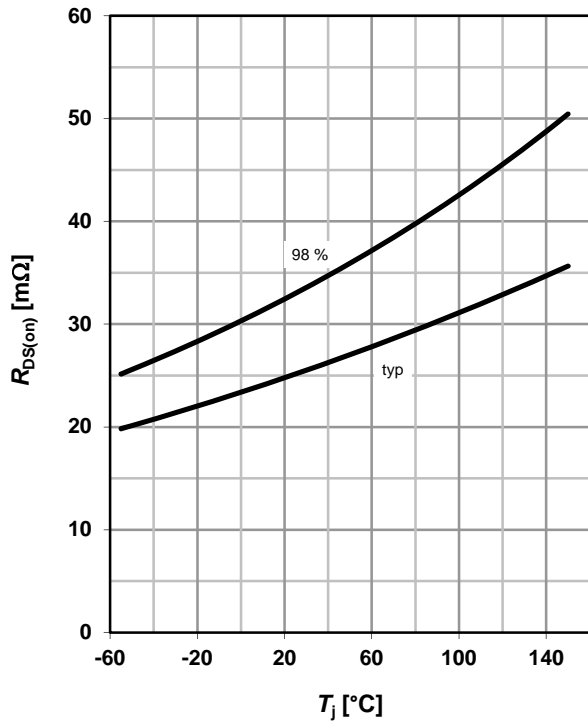
**8 Typ. forward transconductance**

$g_{fs}=f(I_D); T_j=25\text{ }^\circ\text{C}$



**9 Drain-source on-state resistance**

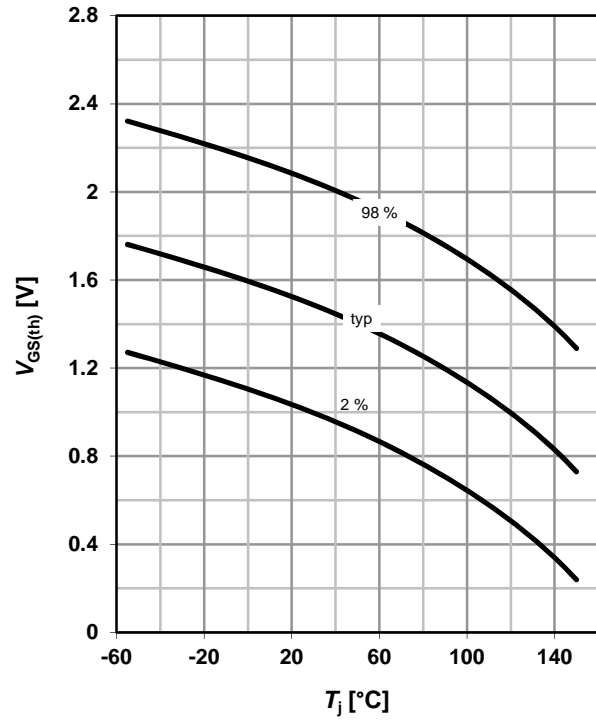
$R_{DS(on)}=f(T_j)$ ;  $I_D=-6.3\text{ A}$ ;  $V_{GS}=-10\text{ V}$



**10 Typ. gate threshold voltage**

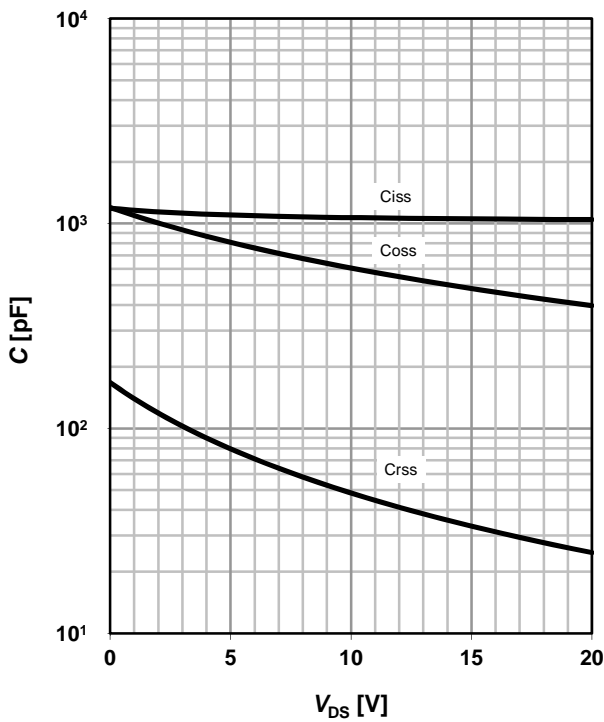
$V_{GS(th)}=f(T_j)$ ;  $V_{DS}=V_{GS}$ ;  $I_D=-30\ \mu\text{A}$

parameter:  $I_D$



**11 Typ. capacitances**

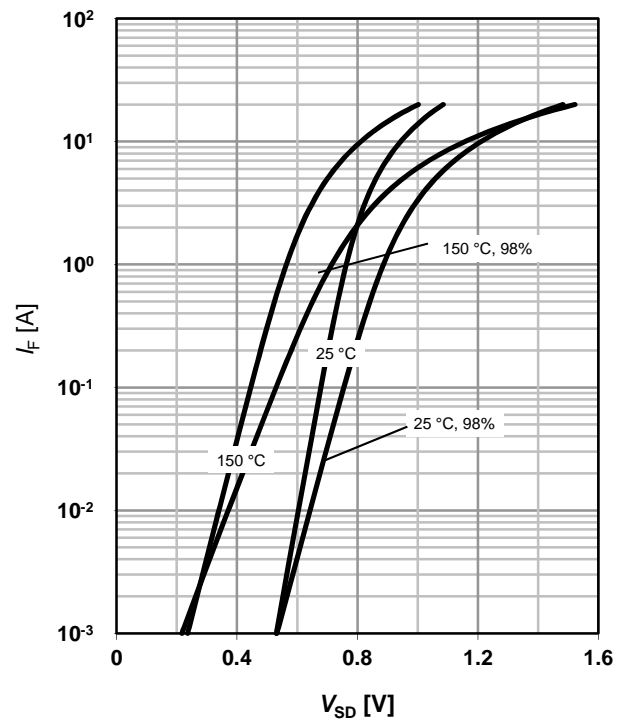
$C=f(V_{DS})$ ;  $V_{GS}=0\text{ V}$ ;  $f=1\text{ MHz}$ ;  $T_j=25^\circ\text{C}$



**12 Forward characteristics of reverse diode**

$I_F=f(V_{SD})$

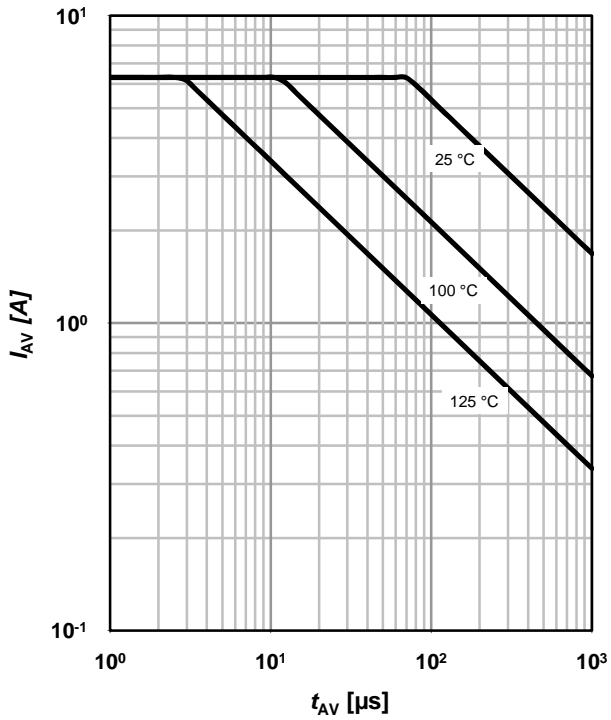
parameter:  $T_j$



**13 Avalanche characteristics**

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

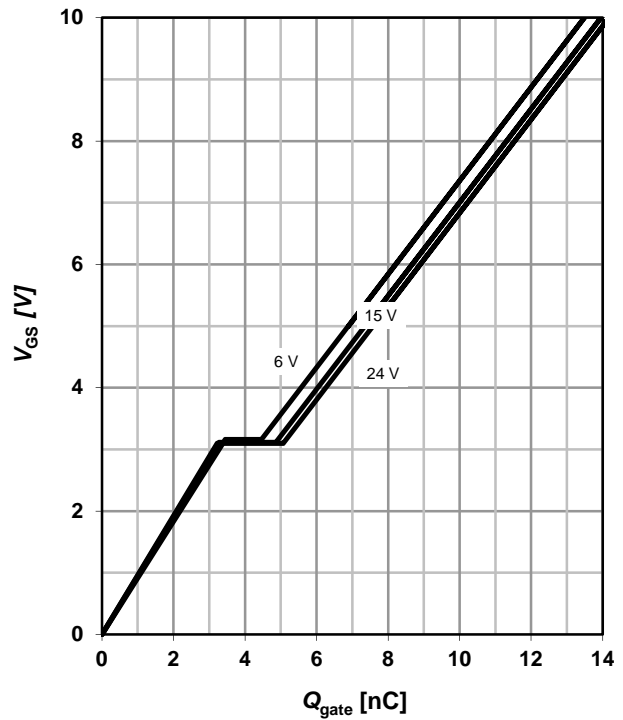
parameter:  $T_{j(\text{start})}$



**14 Typ. gate charge**

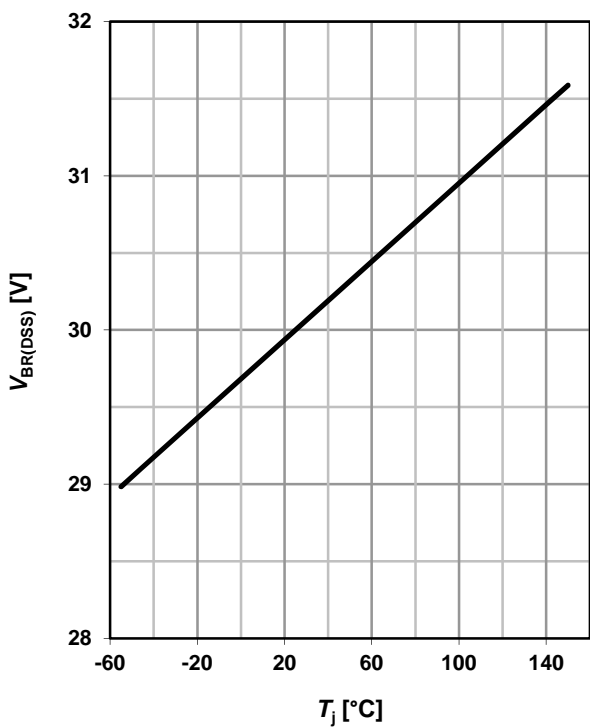
$V_{GS}=f(Q_{\text{gate}}); I_D=-6.3 \text{ A pulsed}$

parameter:  $V_{DD}$

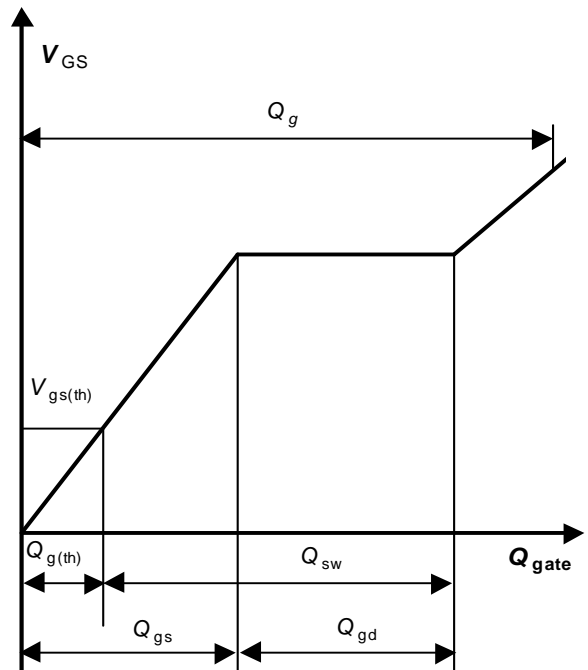


**15 Drain-source breakdown voltage**

$V_{BR(DSS)}=f(T_j); I_D=-250 \mu\text{A}$



**16 Gate charge waveforms**







## Revision History

BSL303SPE

**Revision: 2014-12-10, Rev. 2.0**

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2014-12-10	Release of final version

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